

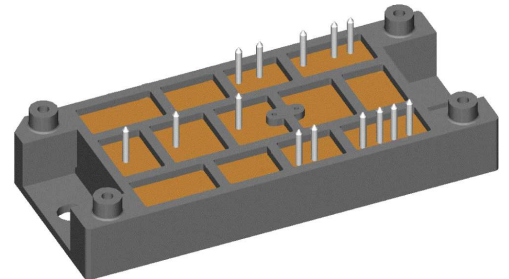
# Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAV} = 180 \text{ A}$	$I_{C25} = 180 \text{ A}$
$I_{FSM} = 1100 \text{ A}$	$V_{CE(sat)} = 1.7 \text{ V}$

## 3~ Rectifier Bridge + Brake Unit

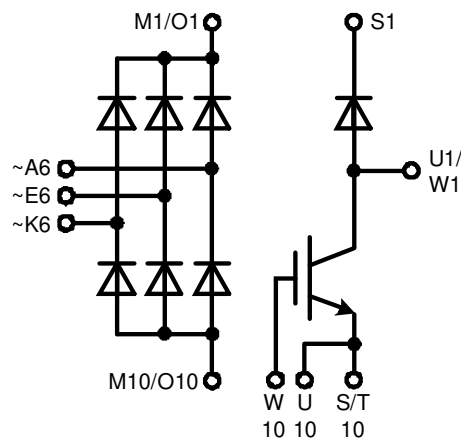
Part number

**VUB120-16NOX**



Backside: isolated

 E72873



### Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- X2PT - 2nd generation Xtreme light Punch Through
- Rugged X2PT design results in:
  - short circuit rated for 10  $\mu\text{sec}$ .
  - very low gate charge
  - low EMI
  - square RBSOA @ 2x  $I_c$
- Thin wafer technology combined with X2PT design results in a competitive low  $V_{CE(sat)}$  and low thermal resistance

### Applications:

- 3~ Rectifier with brake unit for drive inverters

### Package: V2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

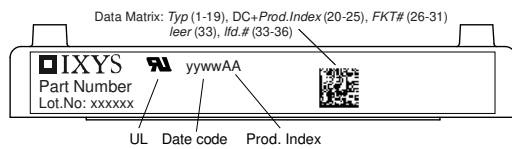
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1600	V
$I_R$	reverse current	$V_R = 1600$ V	$T_{VJ} = 25^\circ\text{C}$			100	$\mu\text{A}$
		$V_R = 1600$ V	$T_{VJ} = 125^\circ\text{C}$			2	mA
$V_F$	forward voltage drop	$I_F = 60$ A	$T_{VJ} = 25^\circ\text{C}$			1.16	V
		$I_F = 180$ A				1.55	V
		$I_F = 60$ A	$T_{VJ} = 125^\circ\text{C}$			1.09	V
		$I_F = 180$ A				1.59	V
$I_{DAV}$	bridge output current	$T_C = 90^\circ\text{C}$ rectangular	$T_{VJ} = 150^\circ\text{C}$ $d = \frac{1}{3}$			180	A
$V_{FO}$	threshold voltage	} for power loss calculation only				0.81	V
$r_F$	slope resistance					4.4	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.6	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.2		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		205	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			1.10	kA
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			1.19	kA
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			935	A
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			1.01	kA
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			6.05	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			5.89	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			4.37	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			4.25	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		37	pF

Brake IGBT + Diode				Ratings					
Symbol	Definition	Conditions	min.	typ.	max.	Unit			
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V			
$V_{GES}$	max. DC gate voltage				$\pm 20$	V			
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V			
$I_{C25}$	collector current	$T_C = 25^{\circ}\text{C}$			180	A			
$I_{C80}$		$T_C = 80^{\circ}\text{C}$			140	A			
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}\text{C}$			500	W			
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 100\text{ A}; V_{GE} = 15\text{ V}$			1.7	V			
					1.9	V			
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{ mA}; V_{GE} = V_{CE}$	6	6.8	7.5	V			
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.1	mA			
					0.1	mA			
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA			
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 100\text{ A}$		340		nC			
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 100\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 6.8\ \Omega$							
$t_r$	current rise time						$T_{VJ} = 125^{\circ}\text{C}$	230	ns
$t_{d(off)}$	turn-off delay time						70	ns	
$t_f$	current fall time						380	ns	
$E_{on}$	turn-on energy per pulse						230	ns	
$E_{off}$	turn-off energy per pulse						12.5	mJ	
		11.5	mJ						
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 6.8\ \Omega$							
$I_{CM}$		$V_{CEK} = 1200\text{ V}$			300	A			
<b>SCSOA</b>	short circuit safe operating area	$V_{CEK} = 1200\text{ V}$							
$t_{SC}$	short circuit duration	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15$			10	$\mu\text{s}$			
$I_{SC}$	short circuit current	$R_G = 6.8\ \Omega$ ; non-repetitive			450	A			
$R_{thJC}$	thermal resistance junction to case				0.25	K/W			
$R_{thCH}$	thermal resistance case to heatsink				0.10	K/W			
Brake Diode									
$V_{RRM}$	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V			
$I_{F25}$	forward current	$T_C = 25^{\circ}\text{C}$			48	A			
$I_{F80}$		$T_C = 80^{\circ}\text{C}$			32	A			
$V_F$	forward voltage	$I_F = 30\text{ A}$			2.75	V			
					1.60	V			
$I_R$	reverse current	$V_R = V_{RRM}$			0.25	mA			
					1	mA			
$Q_{rr}$	reverse recovery charge	$V_R = 600\text{ V}$ $-di_f/dt = 1000\text{ A}/\mu\text{s}$ $I_F = 30\text{ A}; V_{GE} = 0\text{ V}$							
$I_{RM}$	max. reverse recovery current						$T_{VJ} = 125^{\circ}\text{C}$	5.2	$\mu\text{C}$
$t_{rr}$	reverse recovery time						50	A	
$E_{rec}$	reverse recovery energy						300	ns	
					1.9	mJ			
$R_{thJC}$	thermal resistance junction to case				0.9	K/W			
$R_{thCH}$	thermal resistance case to heatsink				0.3	K/W			



Package V2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				76		g
$M_D$	mounting torque		2		2.5	Nm
$d_{Spp/APP}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



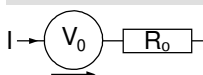
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUB120-16NOX	VUB120-16NOX	Box	6	520475

Similar Part	Package	Voltage class
VUB120-16NOXT	V2-Pack	1600

**Equivalent Circuits for Simulation**

\* on die level

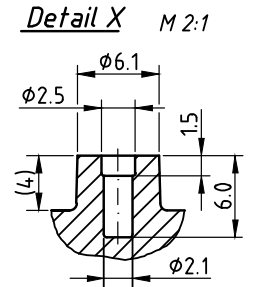
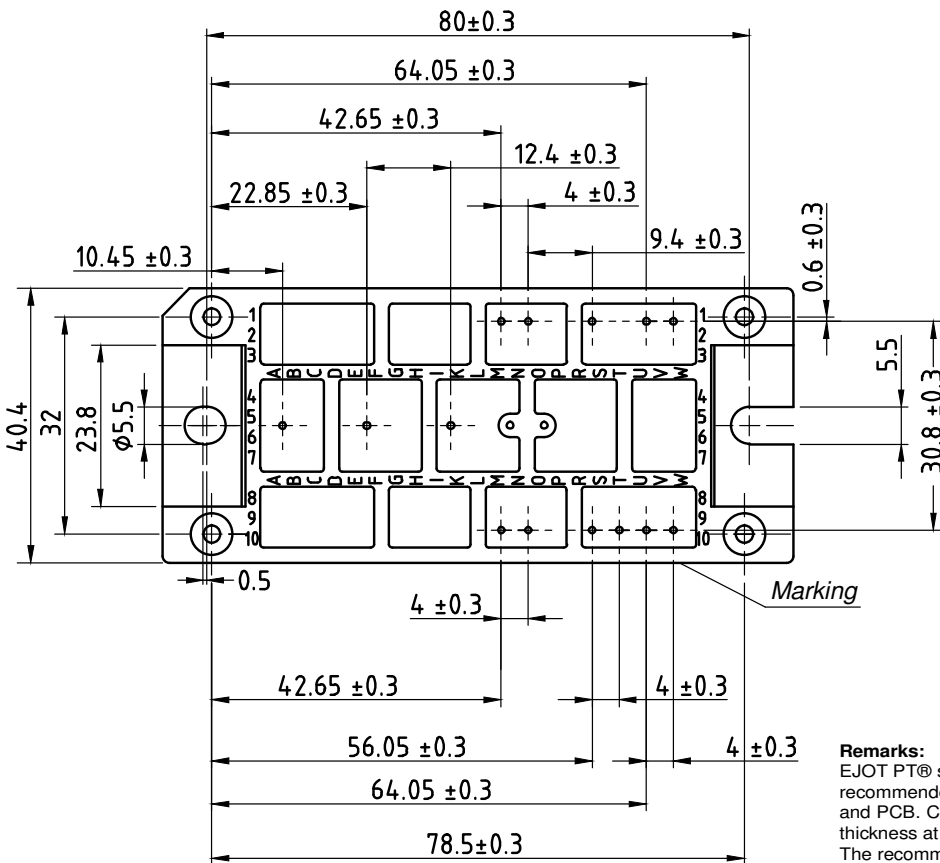
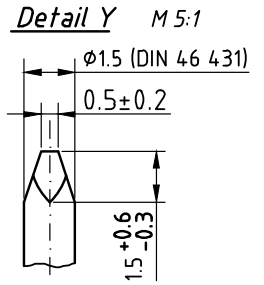
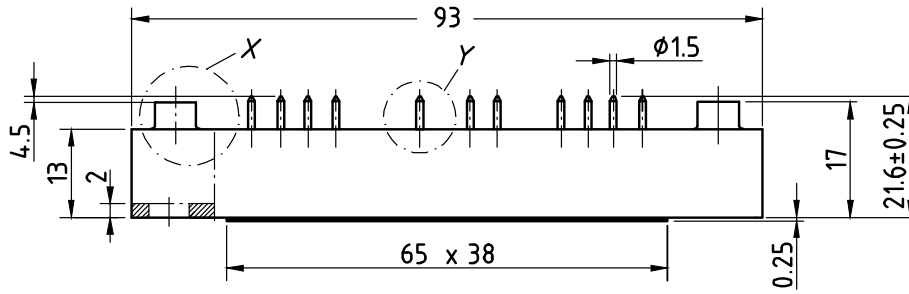
$T_{VJ} = 150^{\circ}\text{C}$



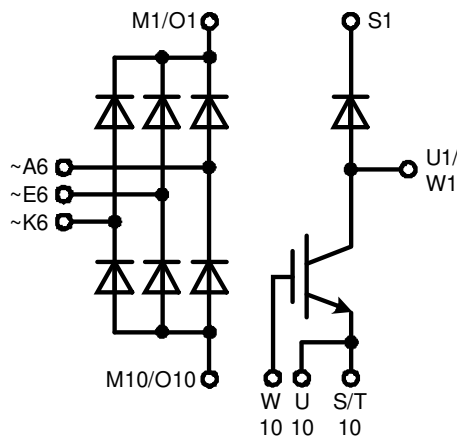
	Rectifier	Brake Diode	
$V_{0 \max}$	0.81	1.31	V
$R_{0 \max}$	3.2	8	mΩ



**Outlines V2-Pack**



**Remarks:**  
EJOT PT® self-tapping screws of the dimension K25 are recommended for the mechanical connection between module and PCB. Choose the right length according to your board thickness at a maximum depth of 6 mm of the module holes. The recommended mounting torque is 1.5 Nm.



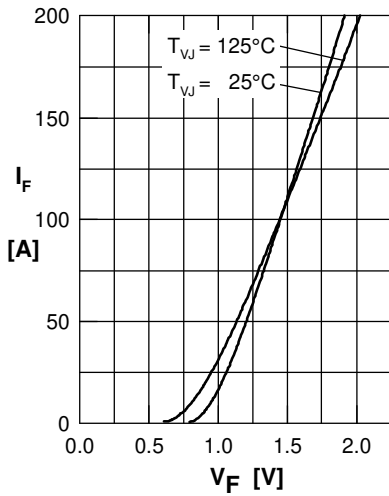
**Rectifier**


Fig. 1 Forward current vs. voltage drop per diode

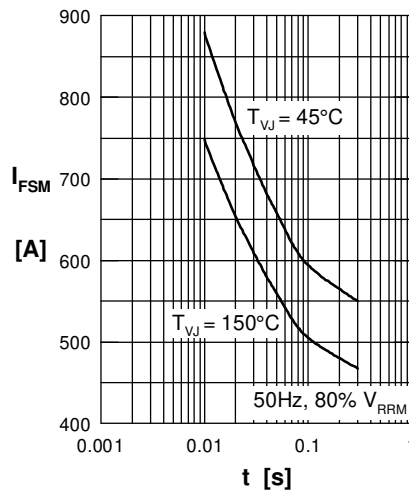


Fig. 2 Surge overload current vs. time per diode

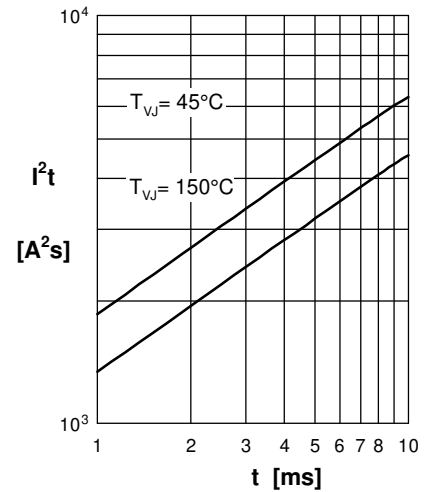
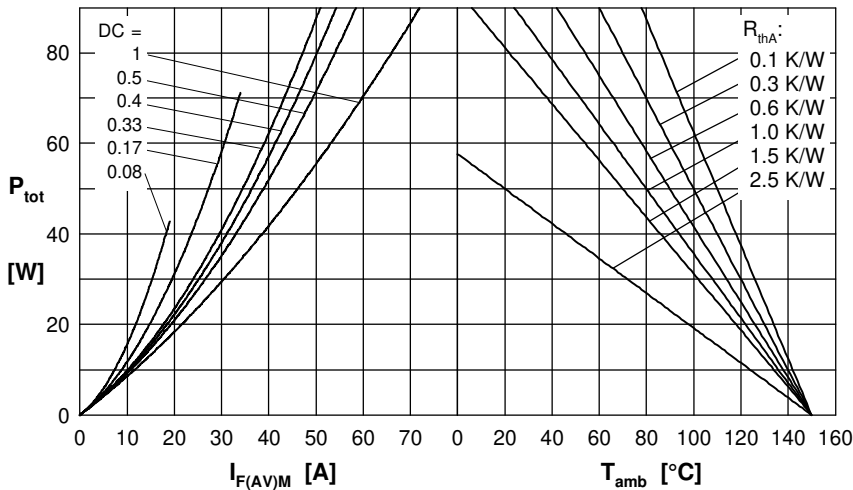

 Fig. 3  $I^2t$  vs. time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

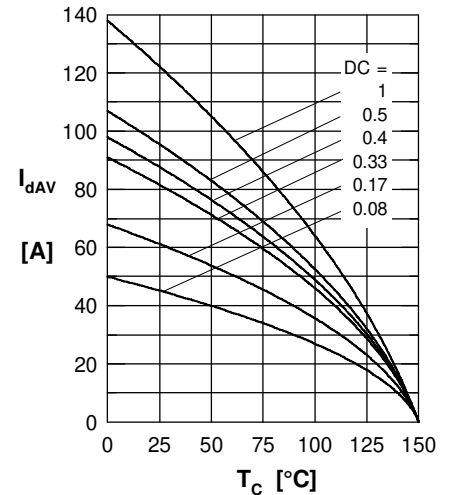


Fig. 5 Max. forward current vs. case temperature per diode

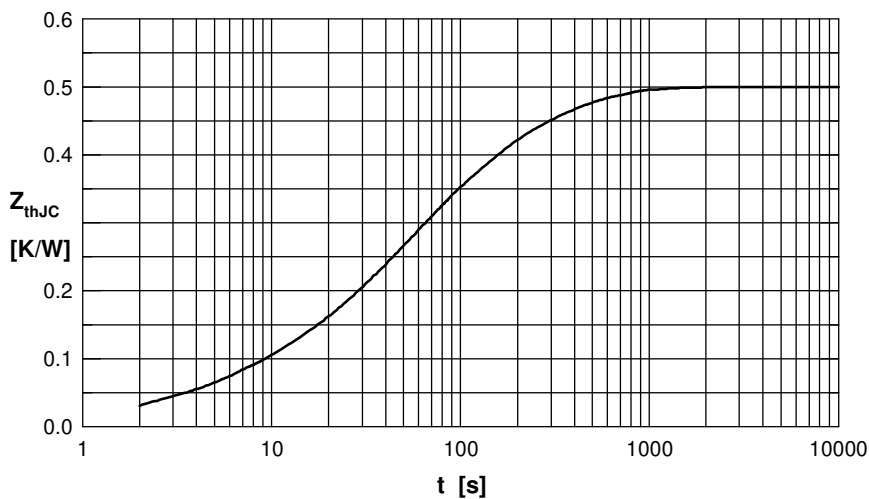


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.040	0.004
2	0.003	0.010
3	0.140	0.030
4	0.120	0.300
5	0.197	0.080

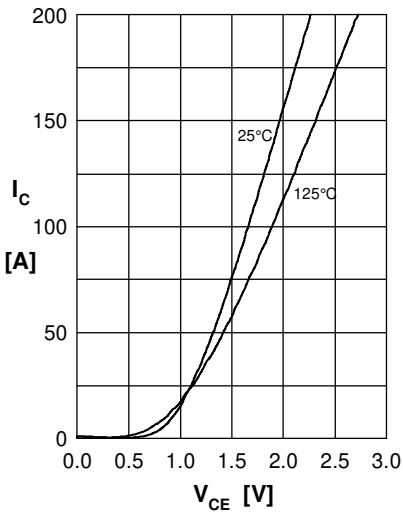
**Brake IGBT + Diode**


Fig. 1 Output characteristics IGBT



Fig. 2 Typ. output characteristics IGBT



Fig. 3 Typ. transfer charact. IGBT



Fig. 4 Typ. turn-on energy &amp; switch. times vs. collector current

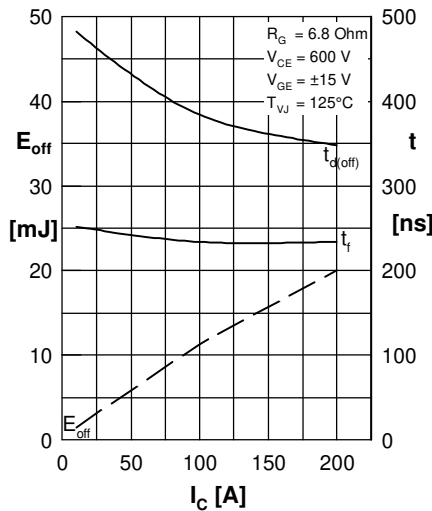


Fig. 5 Typ. turn-off energy &amp; switch. times vs. collector current

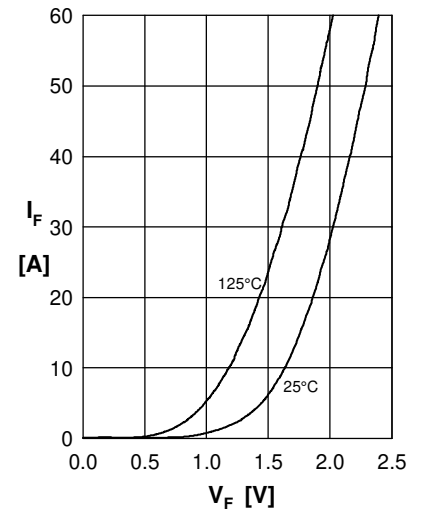


Fig. 6 Typ. forward characteristics Diode

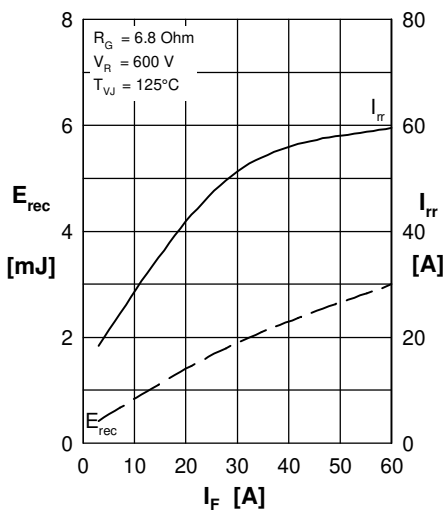


Fig. 7 Typ. reverse recovery characteristics Diode

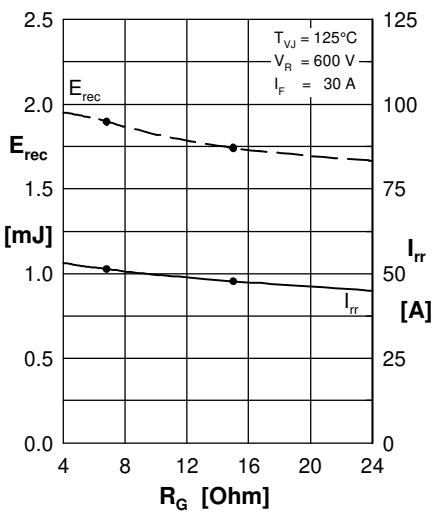


Fig. 8 Typ. reverse recovery characteristics Diode

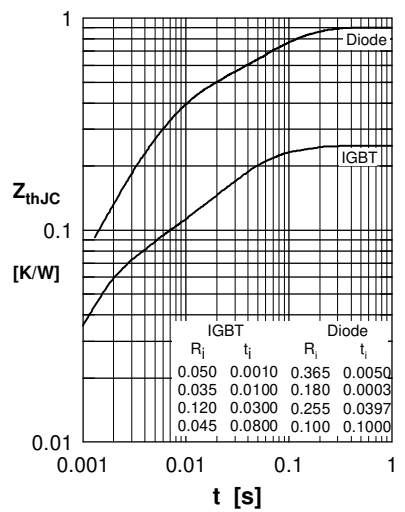


Fig. 9 Transient thermal resistance junction to case

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[FD401R17KF6C\\_B2](#) [FD-DF80R12W1H3\\_B52](#) [FF200R06YE3](#) [FF300R12KE4\\_E](#) [FF450R12ME4P](#) [FF600R12IP4V](#) [FP10R06W1E3\\_B11](#)  
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[F475R07W1H3B11ABOMA1](#) [FD1400R12IP4D](#) [FD200R12PT4\\_B6](#) [FD800R33KF2C-K](#) [FF1200R17KP4\\_B2](#) [FF300R17KE3\\_S4](#)  
[FF300R17ME4\\_B11](#) [FF401R17KF6C\\_B2](#) [FF650R17IE4D\\_B2](#) [FF900R12IP4D](#) [FF900R12IP4DV](#) [STGIF7CH60TS-L](#) [FP50R07N2E4\\_B11](#)  
[FS100R07PE4](#) [FS150R07N3E4\\_B11](#) [FS150R17N3E4](#) [FS150R17PE4](#)